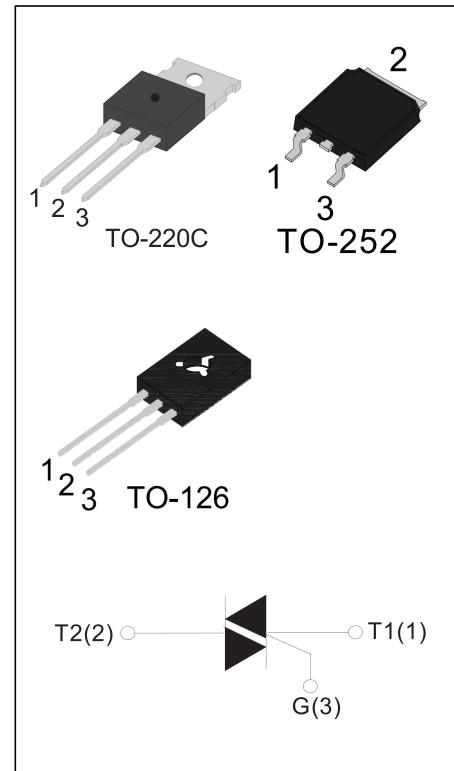


## F0405 Series 4A TRIAC

Rev: 1.0

### MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	4	A
$I_{GT}$	25	mA
$V_{DRM} / V_{RRM}$	600	V



### ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	$T_{stg}$	-40 - 150	°C
Operating junction temperature range	$T_j$	-40 - 125	°C
Repetitive peak off-state voltage( $T_j = 25^\circ\text{C}$ )	$V_{DRM}$	800	V
Repetitive peak reverse voltage( $T_j = 25^\circ\text{C}$ )	$V_{RRM}$	800	V
Non repetitive surge peak Off-state voltage	$V_{DSM}$	$V_{DRM} + 100$	V
Non repetitive peak reverse voltage	$V_{RSM}$	$V_{RRM} + 100$	V
RMS on-state current	$I_{T(RMS)}$	4	A
		TO-220C $T_c = 100^\circ\text{C}$ TO-252 $T_c = 73^\circ\text{C}$ TO-126 $T_c = 73^\circ\text{C}$	

Non repetitive surge peak on-state current (full cycle, F=50Hz)	I <sub>TSM</sub>	25	A
I <sup>2</sup> t value for fusing (tp =10ms)	I <sup>2</sup> t	3.1	A <sup>2</sup> s
Critical rate of rise of on-state current (I <sub>G</sub> =2×I <sub>GT</sub> )	I - II -III	dI/dt	50
	IV		10
Peak gate current	I <sub>GM</sub>	2	A
Average gate power dissipation	P <sub>G(AV)</sub>	0.5	W
Peak gate power	P <sub>GM</sub>	5	W

**ELECTRICAL CHARACTERISTICS (T<sub>j</sub>=25°C unless otherwise specified)**

Symbol	Test Condition	Quadrant		Value			Unit
				05	10	25	
I <sub>GT</sub>	V <sub>D</sub> =12V R <sub>L</sub> =33Ω	I - II -III	MAX	5	5	10	mA
		IV		5	10	25	
V <sub>GT</sub>	ALL		MAX	1.3			V
V <sub>GD</sub>	V <sub>D</sub> =V <sub>DRM</sub> T <sub>j</sub> =125°C R <sub>L</sub> =3.3KΩ	ALL	MIN	0.2			V
I <sub>L</sub>	I <sub>G</sub> =1.2I <sub>GT</sub>	I - III-IV	MAX	8	10	20	mA
		II		12	15	35	
I <sub>H</sub>	I <sub>T</sub> =100mA		MAX	5	10	20	mA
dV/dt	V <sub>D</sub> =2/3V <sub>DRM</sub> Gate Open T <sub>j</sub> =125°C		MIN	20	50	100	V/μs
(dV/dt)c	(dI/dt)c=1.1A/ms T <sub>j</sub> =125°C		MIN	0.5	1	5	V/μs

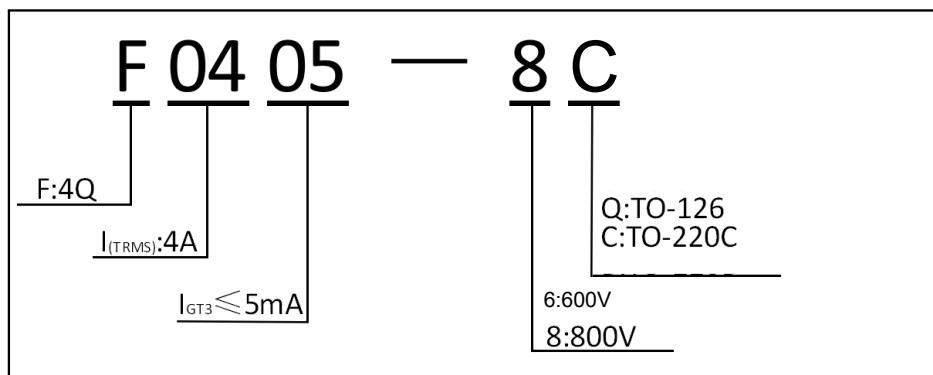
**STATIC CHARACTERISTICS**

Symbol	Parameter		Value	Unit
V <sub>TM</sub>	I <sub>TM</sub> =5A tp=380μs	T <sub>j</sub> =25°C	1.7	V
I <sub>DRM</sub>		T <sub>j</sub> =25°C	5	μA
I <sub>RRM</sub>	V <sub>D</sub> =V <sub>DRM</sub> V <sub>R</sub> =V <sub>RRM</sub>	T <sub>j</sub> =125°C	0.5	mA

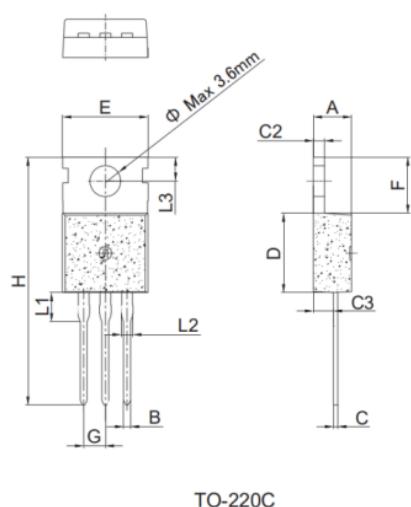
## THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	TO-252	3.7	°C/W
	TO-220C	3.2	
	TO-126	4.1	

## ORDERING INFORMATION

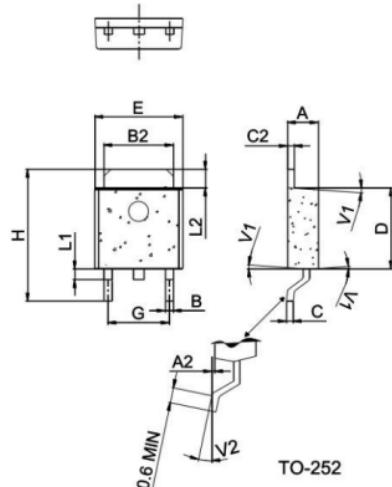


## PACKAGE MECHANICAL DATA

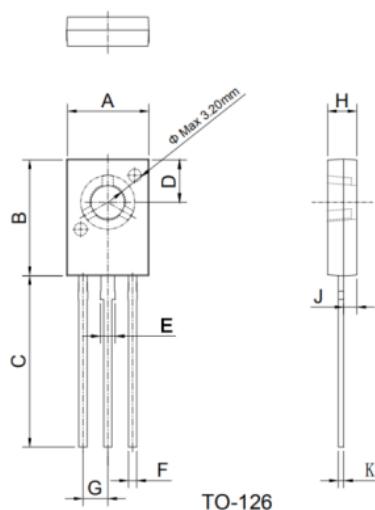


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.70		0.90	0.028		0.035
C	0.45		0.60	0.018		0.024
C2	1.30		1.48	0.048		0.052
C3	2.20		2.60	0.087		0.102
D	8.90		9.90	0.350		0.390
E	9.90		10.3	0.390		0.406
F	6.30		6.90	0.248		0.272
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.39			0.133	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
Φ		3.6			0.142	

## PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	0.03		0.23	0.001		0.009
B	0.55		0.65	0.022		0.026
B2	5.10		5.40	0.200		0.213
C	0.45		0.62	0.018		0.024
C2	0.71		0.99	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G	4.40		4.70	0.173		0.185
H	9.35		10.60	0.368		0.417
L1	1.30		1.70	0.051		0.067
L2	1.37		1.50	0.054		0.059
V1		4°				
V2	0°		8°	0°		8°



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	7.43		8.23	0.292		0.324
B	10.07		11.27	0.396		0.443
C	15.4		17.4	0.606		0.685
D	0.80		4.20	0.149		0.165
E	1.17		1.47	0.046		0.058
F	0.48		0.88	0.018		0.034
G		2.29			0.090	
H	2.50		2.90	0.098		0.114
J	1.10		1.50	0.043		0.059
K	0.45		0.60	0.018		0.024

FIG.1:Maximum power dissipation versus RMS on-state current(full cycle)

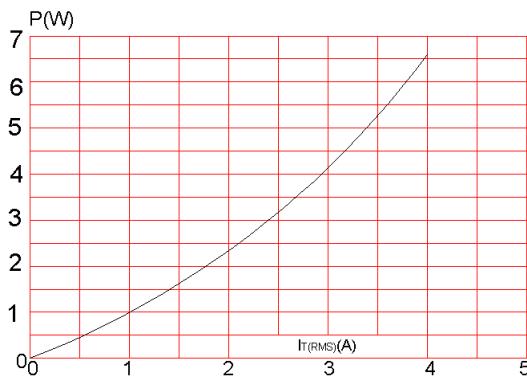


FIG.2:RMS on-state current versus mounting base temperature(full cycle)

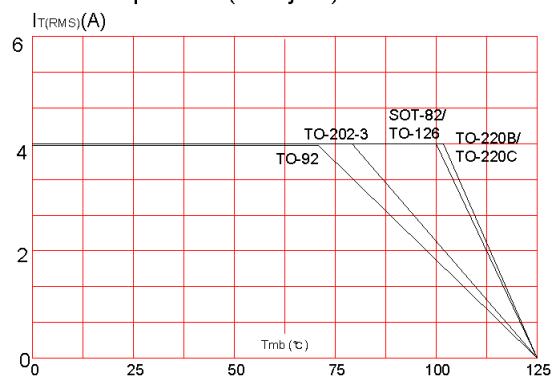


FIG.3:On-state characteristics (maximum values).

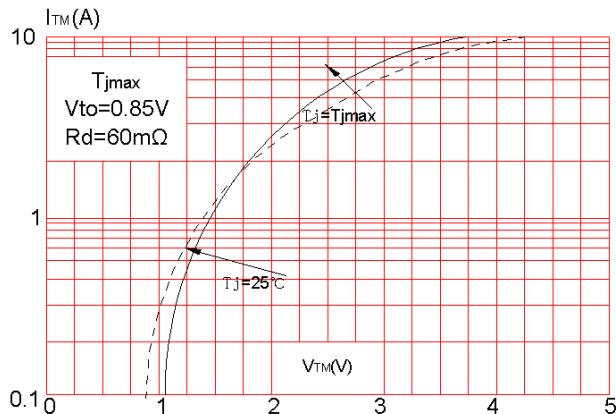


FIG.5:Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 20\text{ms}$ ,and corresponding value of  $I^2t$ .

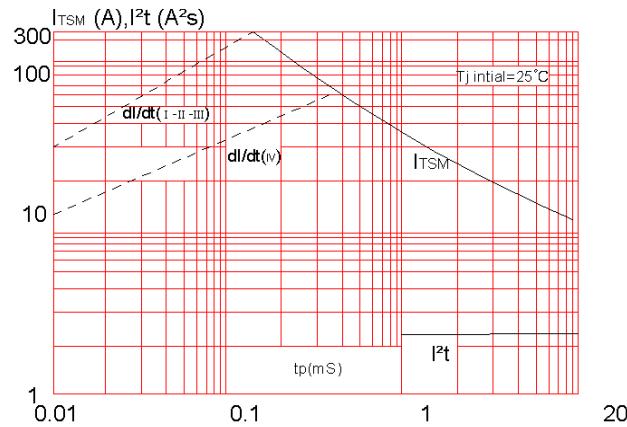


FIG.7:Relative variations of holding current versus junction temperature(typical values)

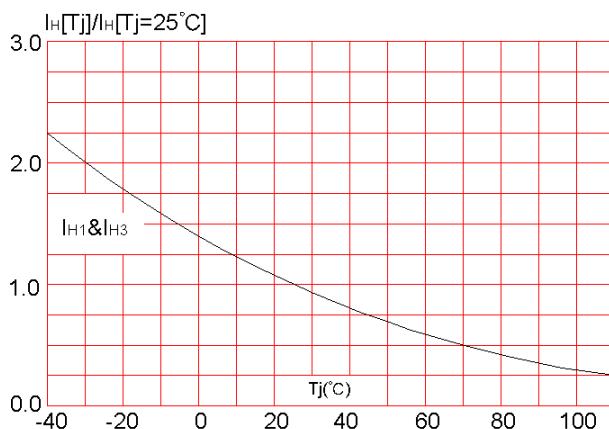


FIG.4:Surge peak on-state current versus number of cycles.

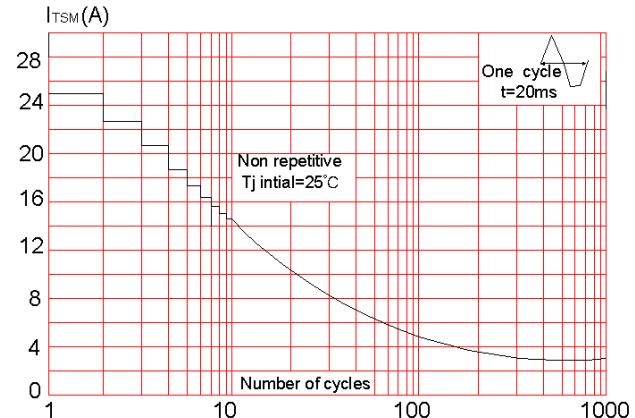


FIG.6:Relative variations of gate trigger current versus junction temperature

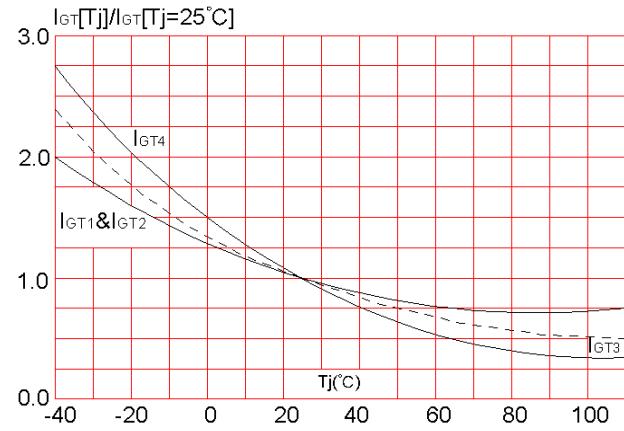
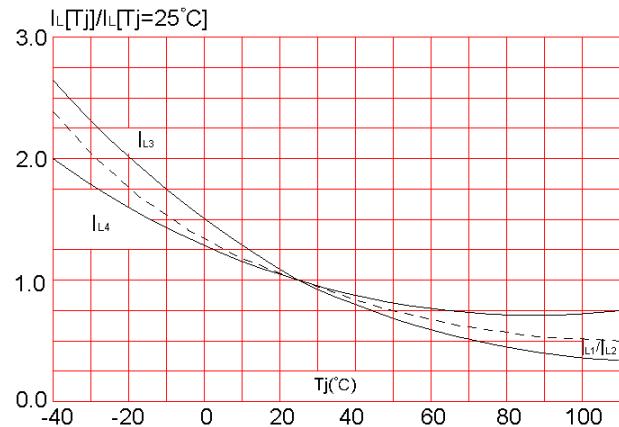


FIG.8:Relative variations of latching current versus junction temperature(typical values)



jilai is a registered trademark of Jiangsu JiLai Microelectronics Co., Ltd.  
Copyright Jiangsu JiLai Microelectronics Co., Ltd. Printed All rights reserved.